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January 2014



# FSB50550T Motion SPM<sup>®</sup> 5 Series

## Features

- UL Certified No. E209204 (UL1557)
- 500 V R<sub>DS(on)</sub> = 1.7 Ω(Max) FRFET MOSFET 3-Phase Inverter with Gate Drivers
- Separate Open-Source Pins from Low-Side MOSFETs for Three-Phase Current-Sensing
- Active-HIGH Interface, Works with 3.3 / 5 V Logic, Schmitt-trigger Input
- Optimized for Low Electromagnetic Interference
- HVIC for Gate Driving and Under-Voltage Protection
- Isolation Rating: 1500 V<sub>rms</sub> / min.
- RoHS Compliant

## Applications

 3-Phase Inverter Driver for Small Power AC Motor Drives

## **Related Source**

- <u>AN-9082 Motion SPM5 Series Thermal Performance</u> <u>by Contact Pressure</u>
- <u>• AN-9080 User's Guide for Motion SPM 5 Series</u> Ver.1

## **General Description**

The FSB50550T is an advanced Motion SPM<sup>®</sup> 5 module providing a fully-featured, high-performance inverter output stage for AC Induction, BLDC and PMSM motors. These modules integrate optimized gate drive of the built-in MOSFETs (FRFET<sup>®</sup> technology) to minimize EMI and losses. The built-in, high-speed HVIC requires only a single supply voltage and translates the incoming logic-level gate inputs to the high-voltage, high-current drive signals required to properly drive the module's internal MOSFETs. Separate open-source MOSFET terminals are available for each phase to support the widest variety of control algorithms.



## Package Marking & Ordering Information

Device	Device Marking	Package	Packing Type	Quantity
FSB50550T	FSB50550T	SPM5F-023	Rail	15

# **Absolute Maximum Ratings**

Inverter Part (each MOSFET unless otherwise specified.)

Symbol	Parameter	Conditions	Rating	Unit
V <sub>DSS</sub>	Drain-Source Voltage of Each MOSFET		500	V
*I <sub>D 25</sub>	Each MOSFET Drain Current, Continuous	$T_{C} = 25^{\circ}C$	1.8	A
*I <sub>D 80</sub>	Each MOSFET Drain Current, Continuous	$T_{C} = 80^{\circ}C$	1.2	A
*I <sub>DP</sub>	Each MOSFET Drain Current, Peak	T <sub>C</sub> = 25°C, PW < 100 μs	3.5	A
*P <sub>D</sub>	Maximum Power Dissipation	$T_{C} = 25^{\circ}C$ , For Each MOSFET	4.5	W

Control Part (each HVIC unless otherwise specified.)

Symbol	Parameter	Conditions	Rating	Unit
V <sub>CC</sub>	Control Supply Voltage	Applied Between $V_{CC}$ and COM	20	V
V <sub>BS</sub>	High-side Bias Voltage	Applied Between $V_B$ and $V_S$	20	V
V <sub>IN</sub>	Input Signal Voltage	Applied Between IN and COM	$-0.3 \sim V_{CC} + 0.3$	V

## **Thermal Resistance**

Symbol	Parameter Conditions		Rating	Unit
$R_{ extsf{ heta}JC}$	Junction to Case Thermal Resistance	Each MOSFET under Inverter Oper- ating Condition (1st Note 1)	8.6	°C/W

## **Total System**

Symbol	Parameter	Parameter Conditions Ra		Unit
TJ	Operating Junction Temperature		-20 ~ 150	°C
T <sub>STG</sub>	Storage Temperature		-50 ~ 150	°C
V <sub>ISO</sub>	Isolation Voltage	60 Hz, Sinusoidal, 1 Minute, Con- nect Pins to Heat Sink Plate	1500	V <sub>rms</sub>

1st Notes:

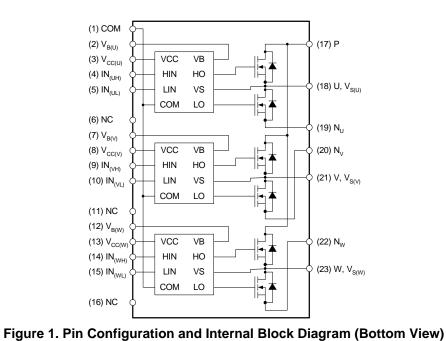
1. For the measurement point of case temperature  ${\rm T}_{\rm C},$  please refer to Figure 4.

2. Marking " \* " is calculation value or design factor.

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# **Pin descriptions**

Pin Number	Pin Name	Pin Description	
1	COM	IC Common Supply Ground	
2	V <sub>B(U)</sub>	Bias Voltage for U Phase High Side MOSFET <sup>®</sup> Driving	
3	V <sub>CC(U)</sub>	Bias Voltage for U Phase IC and Low Side MOSFET Driving	
4	IN <sub>(UH)</sub>	Signal Input for U Phase High-Side	
5	IN <sub>(UL)</sub>	Signal Input for U Phase Low-Side	
6	N.C	No Connectiion	
7	V <sub>B(V)</sub>	Bias Voltage for V Phase High Side MOSFET Driving	
8	V <sub>CC(V)</sub>	Bias Voltage for V Phase IC and Low Side MOSFET Driving	
9	IN <sub>(VH)</sub>	Signal Input for V Phase High-Side	
10	IN <sub>(VL)</sub>	Signal Input for V Phase Low-Side	
11	N.C	No Connectiion	
12	V <sub>B(W)</sub>	Bias Voltage for W Phase High Side MOSFET Driving	
13	V <sub>CC(W)</sub>	Bias Voltage for W Phase IC and Low Side MOSFET Driving	
14	IN <sub>(WH)</sub>	Signal Input for W Phase High-Side	
15	IN <sub>(WL)</sub>	Signal Input for W Phase Low-Side	
16	N.C	No Connectiion	
17	Р	Positive DC–Link Input	
18	U, V <sub>S(U)</sub>	Output for U Phase & Bias Voltage Ground for High Side MOSFET Driving	
19	NU	Negative DC-Link Input for U Phase	
20	NV	Negative DC-Link Input for V Phase	
21	V, V <sub>S(V)</sub>	Output for V Phase & Bias Voltage Ground for High Side MOSFET Driving	
22	N <sub>W</sub>	Negative DC-Link Input for W Phase	
23	W, V <sub>S(W)</sub>	Output for W Phase & Bias Voltage Ground for High Side MOSFET Driving	



#### 1st Notes:

3. Source terminal of each low-side MOSFET is not connected to supply ground or bias voltage ground inside Motion SPM<sup>®</sup> 5 product. External connections should be made as indicated in Figure 3.

Min Typ Max Unit

# **Electrical Characteristics** ( $T_J = 25^{\circ}C$ , $V_{CC} = V_{BS} = 15$ V unless otherwise specified.)

Inverter P	art (each MOSFET unless	otherwise specified.)
Symbol	Parameter	Conditions

-,				- 71-		
BV <sub>DSS</sub>	Drain - Source Breakdown Voltage	V <sub>IN</sub> = 0 V, I <sub>D</sub> = 250 μA (2nd Note 1)	500	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>IN</sub> = 0 V, V <sub>DS</sub> = 500V	-	-	250	μΑ
R <sub>DS(on)</sub>	Static Drain - Source Turn-On Resistance	$V_{CC} = V_{BS} = 15 \text{ V}, V_{IN} = 5 \text{ V}, I_D = 1.2 \text{ A}$	-	1.3	1.7	Ω
$V_{SD}$	Drain - Source Diode Forward Voltage	$V_{CC} = V_{BS} = 15V, V_{IN} = 0 V, I_D = -1.2 A$	-	-	1.2	V
t <sub>ON</sub>			-	560	-	ns
t <sub>OFF</sub>		$V_{PN} = 300 \text{ V}, V_{CC} = V_{BS} = 15 \text{ V}, I_D = 1.2 \text{ A}$	-	440	-	ns
t <sub>rr</sub>	Switching Times	$V_{IN} = 0 V \leftrightarrow 5 V$ , Inductive Load L = 3 mH High- and Low-Side MOSFET Switching	-	130	-	ns
E <sub>ON</sub>		(2nd Note 2)	-	71	-	μJ
E <sub>OFF</sub>			-	11	-	μJ
RBSOA	Reverse Bias Safe Oper- ating Area $V_{PN} = 400 \text{ V}, V_{CC} = V_{BS} = 15 \text{ V}, I_D = I_{DP}, V_{DS} = BV_{DSS}, T_J = 150^{\circ}\text{C}$ High- and Low-Side MOSFET Switching (2nd Note 3)			Full	Square	

Control Part (each HVIC unless otherwise specified.)

Symbol	Parameter		Conditions	Min	Тур	Max	Unit
IQCC	Quiescent V <sub>CC</sub> Current	V <sub>CC</sub> = 15 V, V <sub>IN</sub> = 0 V	Applied Between $V_{CC}$ and COM	-	-	160	μΑ
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> Current	V <sub>BS</sub> = 15 V, V <sub>IN</sub> = 0 V	Applied Between V <sub>B(U)</sub> - U, V <sub>B(V)</sub> - V, V <sub>B(W)</sub> - W	-	-	100	μA
UV <sub>CCD</sub>	Low-Side Under-Voltage	V <sub>CC</sub> Under-Voltage Protection Detection Level		7.4	8.0	9.4	V
UV <sub>CCR</sub>	Protection (Figure 8)	V <sub>CC</sub> Under-Voltage Protection Reset Level		8.0	8.9	9.8	V
UV <sub>BSD</sub>	High-Side Under-Voltage	V <sub>BS</sub> Under-Voltage Protection Detection Level		7.4	8.0	9.4	V
UV <sub>BSR</sub>	Protection (Figure 9)	V <sub>BS</sub> Under-Voltage	Protection Reset Level	8.0	8.9	9.8	V
V <sub>IH</sub>	ON Threshold Voltage	Logic HIGH Level	Applied between IN and COM	2.9	-	-	V
V <sub>IL</sub>	OFF Threshold Voltage	Logic LOW Level	Applied between IN and COM	-	-	0.8	V
I <sub>IH</sub>	Input Pige Current	V <sub>IN</sub> = 5 V		-	10	20	μA
IIL	Input Bias Current	V <sub>IN</sub> = 0 V	Applied between IN and COM	-	-	2	μΑ

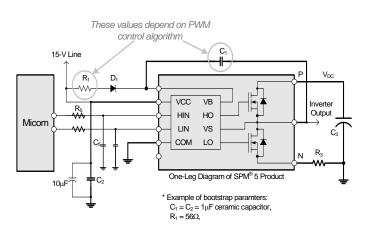
2nd Notes:

1. BV<sub>DSS</sub> is the absolute maximum voltage rating between drain and source terminal of each MOSFET inside Motion SPM<sup>®</sup> 5 product. V<sub>PN</sub> should be sufficiently less than this value considering the effect of the stray inductance so that V<sub>PN</sub> should not exceed BV<sub>DSS</sub> in any case.

2. t<sub>ON</sub> and t<sub>OFF</sub> include the propagation delay of the internal drive IC. Listed values are measured at the laboratory test condition, and they can be different according to the field applications due to the effect of different printed circuit boards and wirings. Please see Figure 4 for the switching time definition with the switching test circuit of Figure 5.

3. The peak current and voltage of each MOSFET during the switching operation should be included in the Safe Operating Area (SOA). Please see Figure 5 for the RBSOA test circuit that is same as the switching test circuit.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V <sub>PN</sub>	Supply Voltage	Applied Between P and N	-	300	400	V
V <sub>CC</sub>	Control Supply Voltage	Applied Between V <sub>CC</sub> and COM	13.5	15.0	16.5	V
V <sub>BS</sub>	High-Side Bias Voltage	Applied Between $V_{B}$ and $V_{S}$	13.5	15.0	16.5	V
V <sub>IN(ON)</sub>	Input ON Threshold Voltage	Applied Between IN and COM	3.0	-	V <sub>CC</sub>	V
V <sub>IN(OFF)</sub>	Input OFF Threshold Voltage	Applied Between IN and COM	0	-	0.6	V
t <sub>dead</sub>	Blanking Time for Preventing Arm-Short	$V_{CC} = V_{BS} = 13.5 \sim 16.5 \text{ V}, \text{ T}_{J} \le 150^{\circ}\text{C}$	1.0	-	-	μs
f <sub>PWM</sub>	PWM Switching Frequency	$T_{J} \leq 150^{\circ}C$	-	15	-	kHz
т <sub>с</sub>	Case Temperature	T <sub>J</sub> ≤ 150°C	-20	-	125	°C

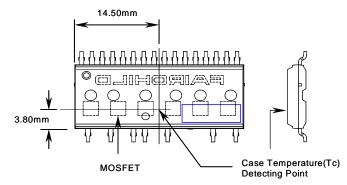


HIN	LIN	Output	Note
0	0	Z	Both FRFET Off
0	1	0	Low side FRFET On
1	0	VDC	High side FRFET On
1	1	Forbidden	Shoot through
Open	Open	Z	Same as (0,0)

## Figure 2. Recommended MCU Interface and Bootstrap Circuit with Parameters

### 3rd Notes:

- 1. It is recommended the bootstrap diode  $\mathsf{D}_1$  to have soft and fast recovery characteristics with 600 V Rating.
- 2. Parameters for bootstrap circuit elements are dependent on PWM algorithm. For 15 kHz of switching frequency, typical example of parameters is shown above.
- 3. RC-coupling (R<sub>5</sub> and C<sub>5</sub>) and C<sub>4</sub> at each input of Motion SPM 5 product and MCU (Indicated as Dotted Lines) may be used to prevent improper signal due to surge-noise.
- 4. Bold lines should be short and thick in PCB pattern to have small stray inductance of circuit, which results in the reduction of surge-voltage. Bypass capacitors such as C<sub>1</sub>, C<sub>2</sub> and C<sub>3</sub> should have good high-frequency characteristics to absorb high-frequency ripple-current.

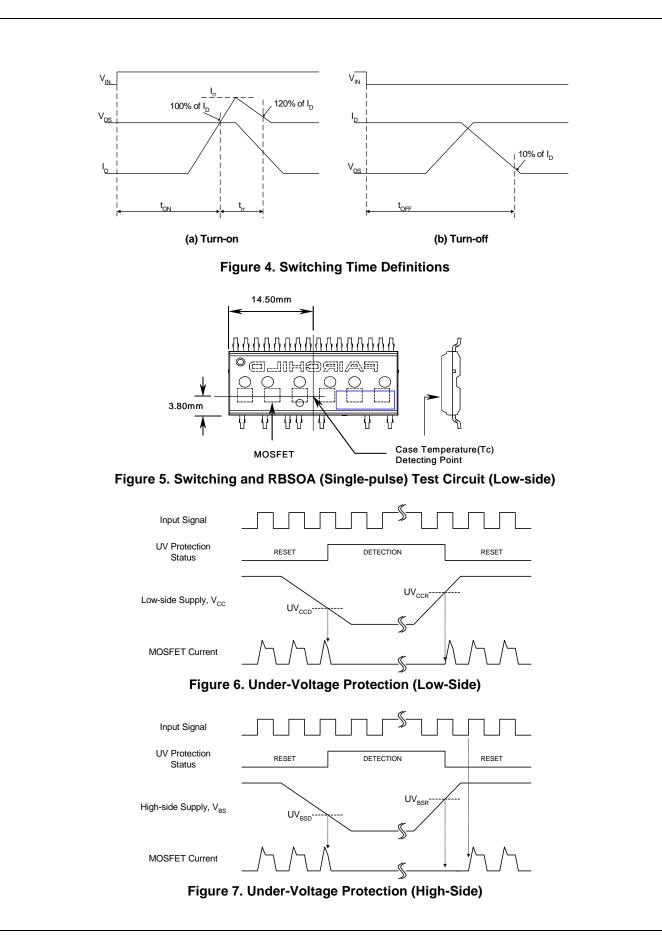


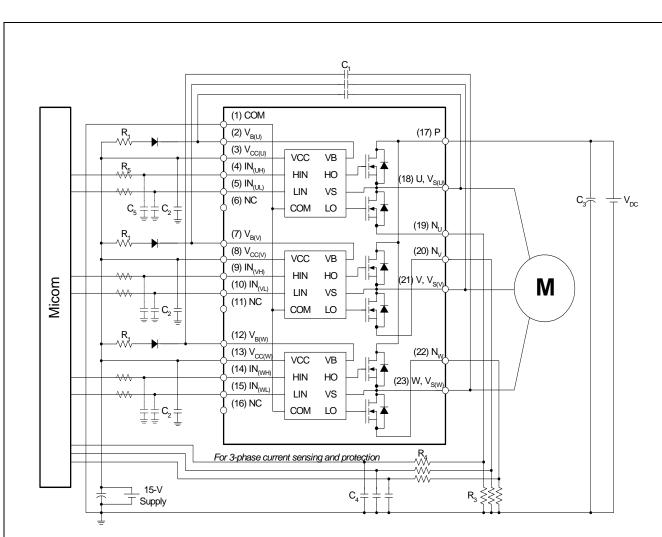
## Figure 3. Case Temperature Measurement

### 3rd Notes:

5. Attach the thermocouple on top of the heat-sink of SPM 5 package (between SPM 5 package and heatsink if applied) to get the correct temperature measurement.

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## Figure 8. Example of Application Circuit

## 4th Notes:

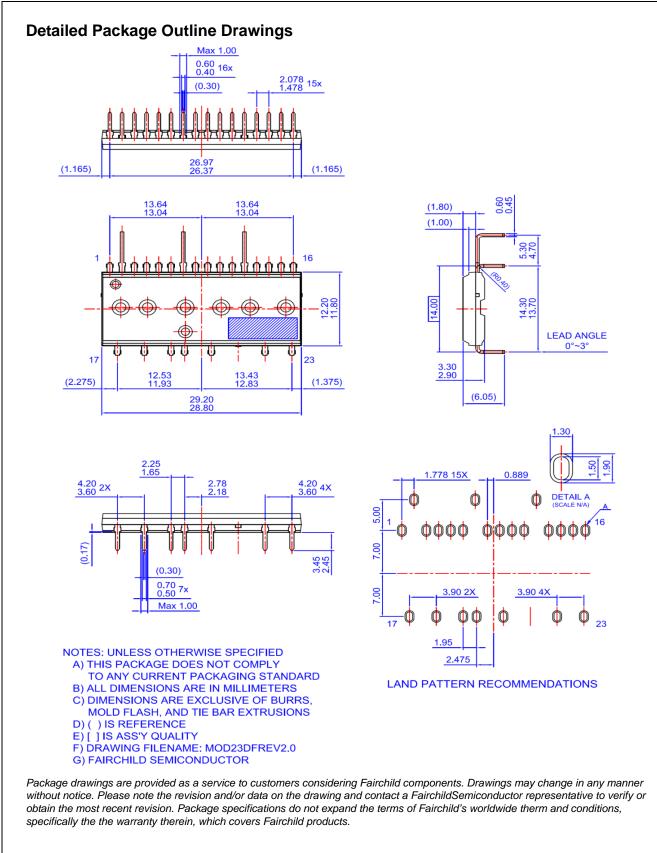
1. About pin position, refer to Figure 1.

2. RC-coupling (R<sub>5</sub> and C<sub>5</sub>, R<sub>4</sub> and C<sub>6</sub>) and C<sub>4</sub> at each input of Motion SPM<sup>®</sup> 5 product and MCU are useful to prevent improper input signal caused by surge-noise.

3. The voltage-drop across R<sub>3</sub> affects the low-side switching performance and the bootstrap characteristics since it is placed between COM and the source terminal of the lowside MOSFET. For this reason, the voltage-drop across R<sub>3</sub> should be less than 1 V in the steady-state.

4. Ground-wires and output terminals, should be thick and short in order to avoid surge-voltage and malfunction of HVIC.

5. All the filter capacitors should be connected close to Motion SPM 5 product, and they should have good characteristics for rejecting high-frequency ripple current.



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http://www.fairchildsemi.com/dwg/MO/MOD23DF.pdf

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